NSN 5961-01-545-0821

Inclosure Material:

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Glass
Overall Length:
Between 0.150 inches and 0.170 inches
Terminal Length:
1.000 inches
Overall Diameter:
Between 0.064 inches and 0.070 inches
Function For Which Designed:
General purpose
End Application:
Nimitz class cvn r-2199a/sps-4 (v), receiver, radar
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
15
Mounting Method:
Terminal
Terminal Circle Diameter:
0.4 millimeters
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
100.0 breakdown voltage, dc
Current Rating Per Characteristic:
30.00 milliamperes source cutoff current preset
Power Rating Per Characteristic:
250.0 milliwatts any acceptable
Capacitance Rating In Picofarads:
0.3
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius junction
Product Name:
Pin diode for rf switching and attenuating
Special Features:
Lead finish is 95-5 tin-lead; leads are restricted so that the bend starts at least 1/16 in. From the glass body; effective carrier lifetime: 100
ns (min); max. Residual series resistance: 15 ohms; high resistance limit: 1100-1660 ohms; low resistance limit: 10-24 ohms; max.
Soldering temp: 250 degrees c for 5 sec
Terminal Type And Quantity:
2 uninsulated wire lead
Shelf Life:
N/a
Unit Of Measure:

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Demilitarization:

No

Fiig:

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